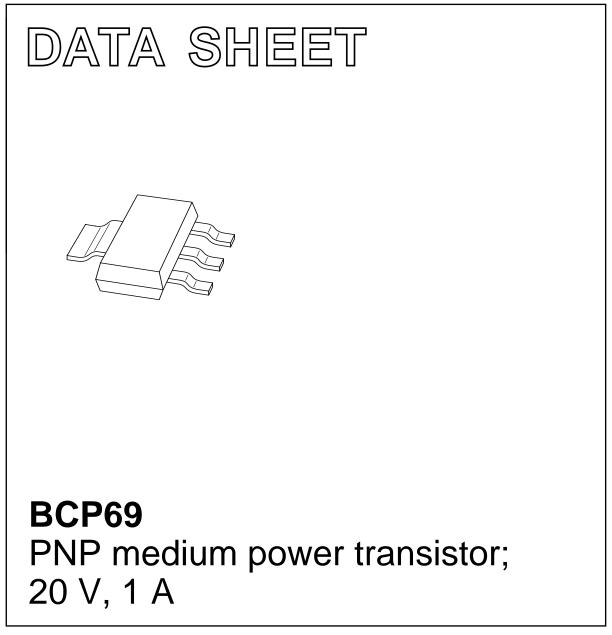
DISCRETE SEMICONDUCTORS



Product specification Supersedes data of 2002 Nov 15 2003 Nov 25



Semiconductors

Philips

PNP medium power transistor; 20 V, 1 A

FEATURES

- High current
- Three current gain selections
- 1.4 W total power dissipation.

APPLICATIONS

- Linear voltage regulators (LDO)
- High side switches
- Supply line switches
- MOSFET drivers
- Audio pre-amplifiers.

DESCRIPTION

PNP medium power transistor (see "Simplified outline, symbol and pinning") for package details.

PRODUCT OVERVIEW

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _{CEO}	collector-emitter	-	-20	V
	voltage			
I _C	collector current (DC)	-	-1	А
I _{CM}	peak collector current	-	-2	А
h _{FE}	DC current gain			
	BCP69	85	375	
	BCP69-16	100	250	
	BCP69-16/IN	140	230	
	BCP69-25	160	375	

TYPE NUMBER	PACH	AGE	MARKING CODE
	PHILIPS	EIAJ	MARKING CODE
BCP69	SOT223	SC-73	BCP69
BCP69-16	SOT223	SC-73	BCP69/16
BCP69-16/IN	SOT223	SC-73	69-16N
BCP69-25	SOT223	SC-73	BCP69/25

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL		PINNING		
I TPE NUMBER			DESCRIPTION		
BCP69	4	1	base		
	2,4	2	collector		
		3	emitter		
	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	4	collector		

PNP medium power transistor; 20 V, 1 A

RELATED PRODUCTS

TYPE NUMBER	DESCRIPTION	FEATURE
BCP68	NPN medium power transistor	NPN complement
BC869	PNP medium power transistor	SOT89, -20 V
BC369	PNP medium power transistor	SOT54, -20 V

ORDERING INFORMATION

		PACKAGE	
I TPE NUMBER	NAME	DESCRIPTION	VERSION
BCP69	_	plastic surface mounted package; collector pad for good heat	SOT223
BCP69-16		transfer; 4 leads	
BCP69-16/IN			
BCP69-25			

LIMITING VALUES

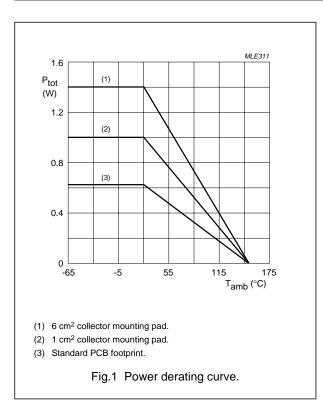
In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	-	-32	V
V _{CEO}	collector-emitter voltage	open base	-	-20	V
V _{EBO}	emitter-base voltage	open collector	-	-5	V
I _C	collector current (DC)		-	-1	A
I _{CM}	peak collector current		-	-2	A
I _{BM}	peak base current		-	-200	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$; notes 1 and 2	-	0.625	W
		$T_{amb} \le 25 \ ^{\circ}C$; notes 1 and 3	-	1	W
		$T_{amb} \le 25 \ ^{\circ}C$; notes 1 and 4	-	1.4	W
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Notes

- 1. See SOT223 (SC-73) standard mounting conditions.
- 2. Device mounted on a FR4 printed-circuit board; single-sided copper; tinplated; standard footprint for SOT223.
- 3. Device mounted on a FR4 printed-circuit board; single-sided copper; tinplated; 1 cm² collector mounting pad.
- 4. Device mounted on a FR4 printed-circuit board; single-sided copper; tinplated; 6 cm² collector mounting pad.

PNP medium power transistor; 20 V, 1 A



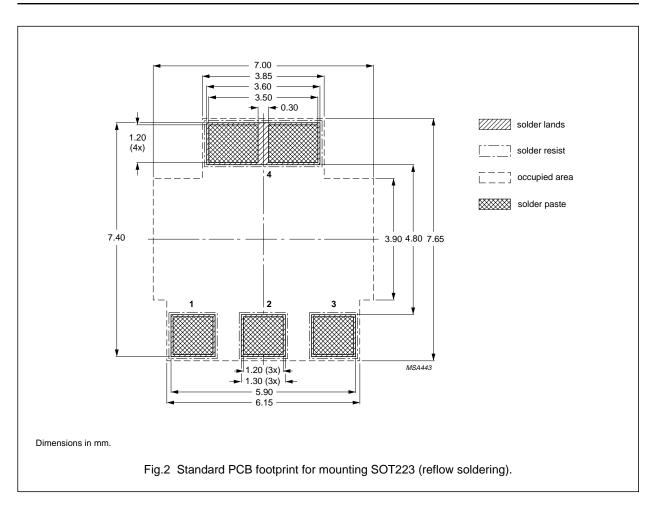
THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to	$T_{amb} \le 25 \ ^{\circ}C$; notes 1 and 2	200	K/W
ambient		$T_{amb} \le 25 \ ^{\circ}C$; notes 1 and 3	125	K/W
		$T_{amb} \le 25 \ ^{\circ}C$; notes 1 and 4	89	K/W
R _{th(j-s)}	thermal resistance from junction to solder point	$T_{amb} \le 25 \ ^{\circ}C$	15	K/W

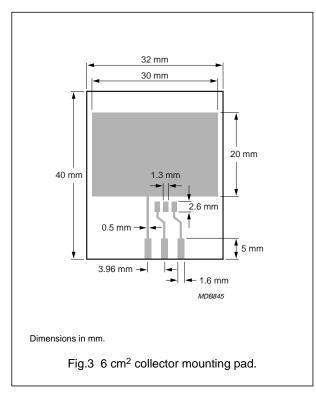
Notes

- 1. See SOT223 (SC-73) standard mounting conditions.
- 2. Device mounted on a FR4 printed-circuit board; single-sided copper; tinplated; standard footprint for SOT223.
- 3. Device mounted on a FR4 printed-circuit board; single-sided copper; tinplated; 1 cm² collector mounting pad.
- 4. Device mounted on a FR4 printed-circuit board; single-sided copper; tinplated; 6 cm² collector mounting pad.

PNP medium power transistor; 20 V, 1 A



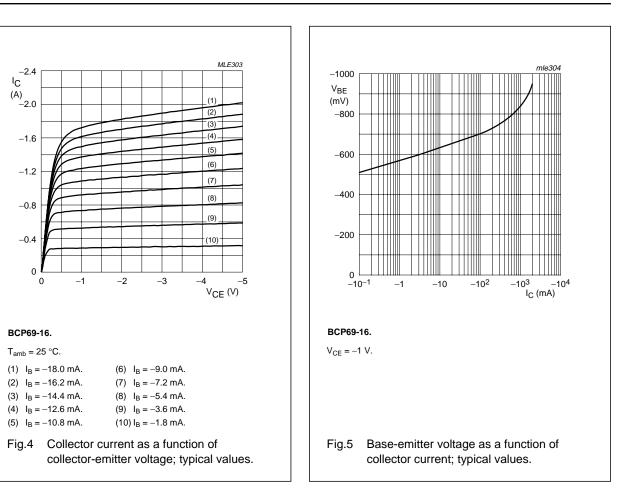
PNP medium power transistor; 20 V, 1 A



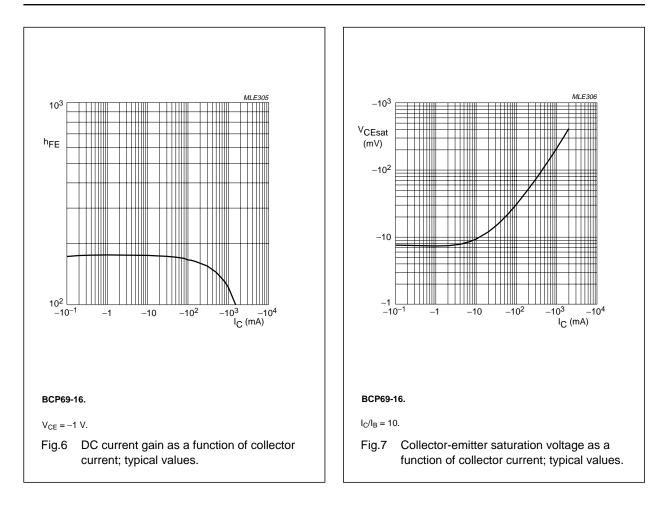
CHARACTERISTICS

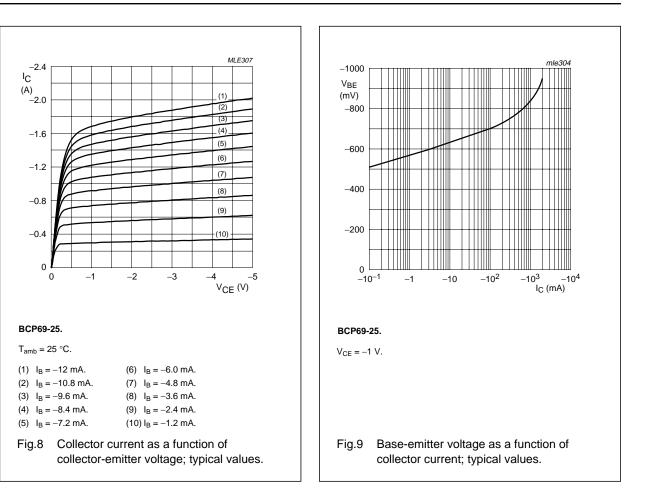
 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	$V_{CB} = -25 \text{ V}; I_E = 0$	-	-	-100	nA
		V _{CB} = -25 V; I _E = 0; T _j = 150 °C	-	-	-10	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0$	-	-	-100	nA
h _{FE}	DC current gain	BCP69				
		$V_{CE} = -10 \text{ V}; \text{ I}_{C} = -5 \text{ mA}$	50			
		$V_{CE} = -1 \text{ V}; I_{C} = -500 \text{ mA}$	85	-	375	
		$V_{CE} = -1 V; I_C = -1 A$	60	-	-	
		BCP69-16				
		$V_{CE} = -1 \text{ V}; \text{ I}_{C} = -500 \text{ mA}$	100	-	250	
		BCP69-16/IN				
		$V_{CE} = -1 \text{ V}; \text{ I}_{C} = -500 \text{ mA}$	140		230	
		BCP69-25				
		$V_{CE} = -1 \text{ V}; I_{C} = -500 \text{ mA}$	160		375	
V _{CEsat}	collector-emitter saturation voltage	$I_{\rm C} = -1$ A; $I_{\rm B} = -100$ mA	-	-	-500	mV
V _{BE}	base-emitter voltage	$V_{CE} = -10 \text{ V}; I_{C} = -5 \text{ mA}$	-	-	-700	mV
		$V_{CE} = -1 V; I_C = -1 A$	-	-	-1	V
Cc	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0; f = 1 \text{ MHz}$	-	28	-	pF
f _T	transition frequency	$V_{CE} = -5 \text{ V}; I_{C} = -50 \text{ mA}; f = 100 \text{ MHz}$	40	140	-	MHz



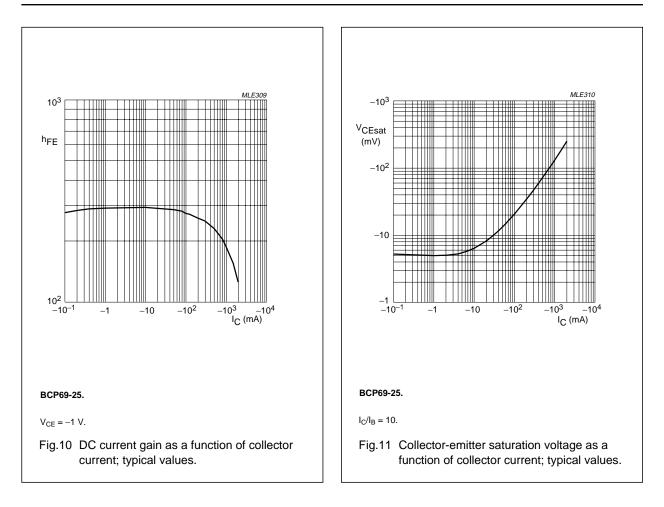


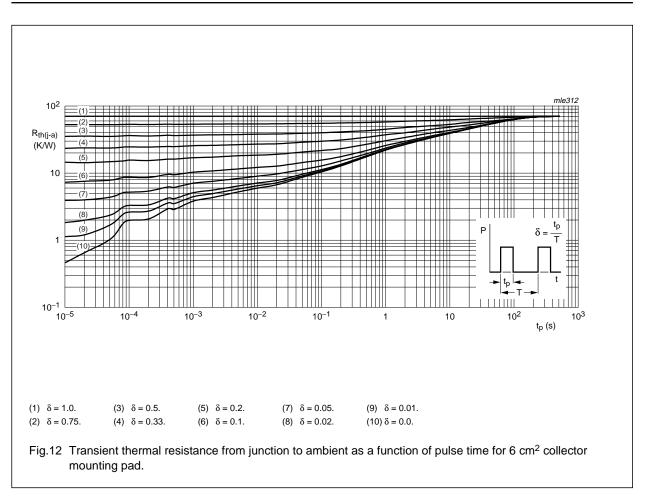




BCP69

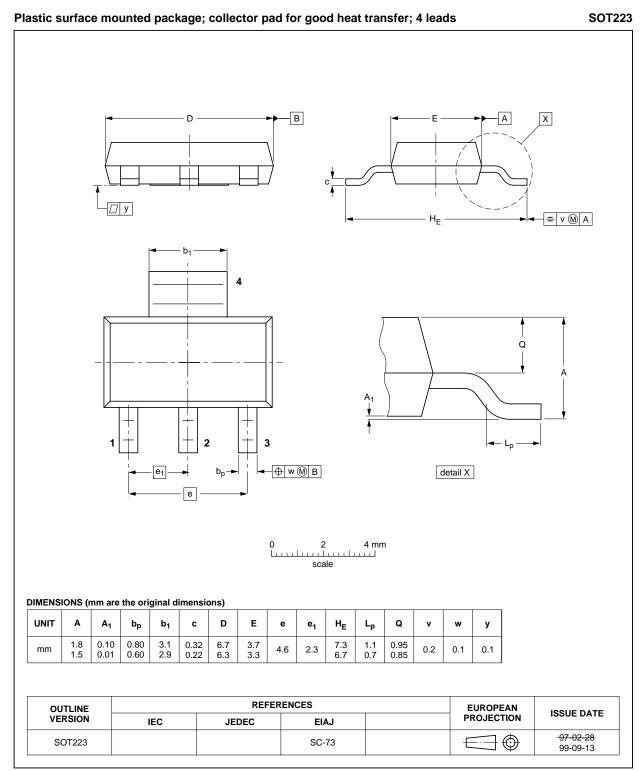






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PACKAGE OUTLINE



BCP69

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
11	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

Notes

- 1. Please consult the most recently issued data sheet before initiating or completing a design.
- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.
- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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